

S3ABF THRU S3MBF

Surface Mount General Purpose Silicon Rectifiers

Reverse Voltage - 50 to 1000 V

Forward Current - 3 A

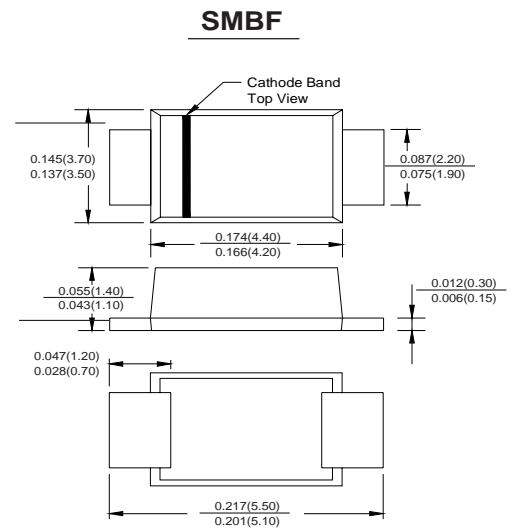


FEATURES

- For surface mounted applications
- Low profile package
- Glass Passivated Chip Junction
- Superfast reverse recovery time
- Lead free in comply with EU RoHS 2011/65/EU directives

MECHANICAL DATA

- Case: SMBF
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 57mg / 0.002oz



Maximum Ratings and Electrical characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20 %.

Parameter	Symbols	S3ABF	S3BBF	S3DBF	S3GBF	S3JBF	S3KBF	S3MBF	Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current at $T_a = 65\text{ }^\circ\text{C}$	$I_{F(AV)}$	3							A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	I_{FSM}	100							A
Maximum Instantaneous Forward Voltage at 3 A	V_F	1.2							V
Maximum DC Reverse Current $T_a = 25\text{ }^\circ\text{C}$ at Rated DC Blocking Voltage $T_a = 125\text{ }^\circ\text{C}$	I_R	5 250							μA
Typical Junction Capacitance ¹⁾	C_j	53							pF
Typical Thermal Resistance ²⁾	$R_{\theta JA}$	13 47							$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_j, T_{stg}	-55 ~ +150							$^\circ\text{C}$

1) Measured at 1 MHz and applied reverse voltage of 4 V D.C

2) Thermal resistance from junction to ambient at 0.375" (9.5 mm) lead length, P.C.B. mounted



Fig.1 Forward Current Derating Curve

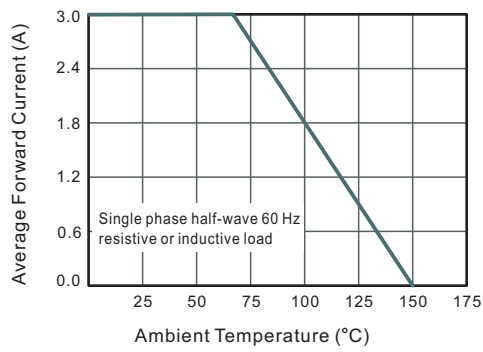


Fig.2 Typical Instantaneous Reverse Characteristics

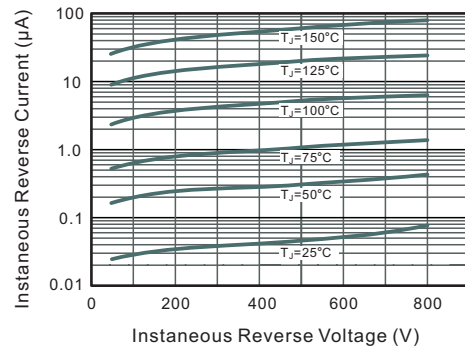


Fig.3 Typical Forward Characteristic

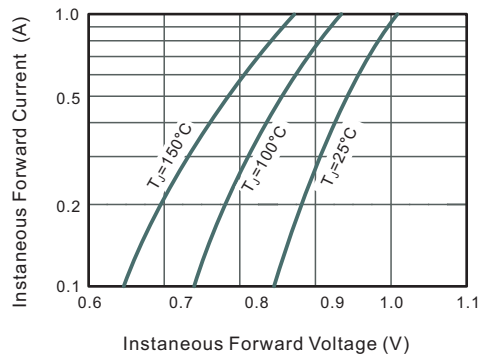


Fig.4 Typical Junction Capacitance

